IN THE SPECIFICATION

Please amend the paragraph beginning on page 1, line 4 as follows:

This application is related to the following co-pending and commonly assigned applications; attorney docket number 303.672US1, application serial number 09/483881, entitled "Selective Electroless-Plated Copper Metallization," and attorney docket number 1303.013US1, application serial number 09/854540 ~~serial number XX~~, entitled "Copper Dual Damascene Interconnect Technology," which are hereby incorporated by reference. The latter of these addresses a selective chemical vapor deposition process.

A1

Please amend the paragraph beginning on page 6, line 22 as follows:

Figures 2A-2K are cross-sectional views illustrating a sequence of fabrication steps for forming a dual damascene copper interconnect in association with a semiconductor device according to the teachings of the present invention. Figure 2A depicts a portion of an insulating layer 251 formed over a semiconductor substrate 250, on or within which a metal layer 252 has been formed. The metal layer 252 represents a lower metal interconnect layer which is to be later interconnected with an upper copper interconnect layer. The metal layer 252 may ~~for~~ be formed of copper (Cu), but other conductive materials, such as tungsten (W) or aluminum (Al) and their alloys, may be used also.

A2

Please amend the paragraph beginning on page 7, line 12 as follows:

In one embodiment, the first intermetal insulating layer 255 is be formed of a conventional insulating oxide, such as silicon oxide (SiO_2). In alternative embodiments, the first intermetal insulating layer 255 is formed of a low dielectric constant material such as, for example, polyimide, spin-on-polymers (SOP), parylene, flare, polyarylethers, polytetrafluoroethylene, benzocyclobutene (BCB), spin-on low-k dielectric resins such as SILK resins, fluorinated silicon oxide (FSG), porous siloxane-based polymer such as NANOGLASS polymer or hydrogen silsesquioxane, among others. The present invention is not limited, however, to the above-listed materials and other insulating and/or dielectric materials known in the industry may be used also.

A3

IN THE DRAWINGS

The office action objected to FIGS. 1A-1C, and required the legend PRIOR ART on these figures. Corrected drawings that include the legend PRIOR ART on FIGS. 1A-1C are provided with this Response. Applicant respectfully requests withdrawal of the rejection.